



**THE DATASHEET OF  
FDD6690A**



May 2024

# FDD6690A

## 30V N-Channel PowerTrench<sup>®</sup> MOSFET

### General Description

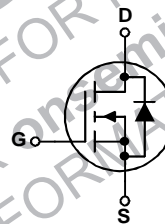
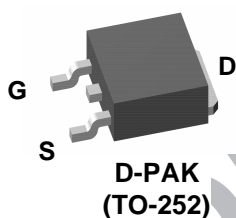
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on state resistance and yet maintain low gate charge for superior switching performance.

### Applications

- DC/DC converter
- Motor Drives

### Features

- 46 A, 30 V  $R_{DS(ON)} = 12\text{ m}\Omega @ V_{GS} = 10\text{ V}$   
 $R_{DS(ON)} = 14\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- Low gate charge
- Fast Switching Speed
- High performance trench technology for extremely low  $R_{DS(ON)}$



### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage	30	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current @ T <sub>C</sub> =25°C (Note 3)	46	A
	@ T <sub>A</sub> =25°C (Note 1a)	12	
	Pulsed (Note 1a)	100	
P <sub>D</sub>	Power Dissipation @ T <sub>C</sub> =25°C (Note 3)	56	W
	@ T <sub>A</sub> =25°C (Note 1a)	3.3	
	@ T <sub>A</sub> =25°C (Note 1b)	1.5	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 to +175	°C

### Thermal Characteristics

R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Note 1)	2.7	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	45	
R <sub>θJA</sub>	(Note 1b)	96	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape width	Quantity
FDD6690A	FDD6690A	D-PAK (TO-252)	13"	16mm	2500 units

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Drain-Source Avalanche Ratings** (Note 2)

$E_{AS}$	Drain-Source Avalanche Energy	Single Pulse, $V_{DD} = 15\text{ V}$ , $I_D = 12\text{ A}$			180	mJ
$I_{AS}$	Drain-Source Avalanche Current				12	A

**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_D = 250\ \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		24		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 100$	nA

**On Characteristics** (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 12\text{ A}$ $V_{GS} = 4.5\text{ V}$ , $I_D = 10\text{ A}$ $V_{GS} = 10\text{ V}$ , $I_D = 12\text{ A}$ , $T_J = 125^\circ\text{C}$		7.7 9.9 11.4	12 14 19	m $\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}$ , $V_{DS} = 5\text{ V}$	50			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}$ , $I_D = 12\text{ A}$		47		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance			1230		pF
$C_{oss}$	Output Capacitance	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		325		pF
$C_{rss}$	Reverse Transfer Capacitance			150		pF
$R_G$	Gate Resistance	$V_{GS} = 15\text{ mV}$ , $f = 1.0\text{ MHz}$		1.5		pF

**Switching Characteristics** (Note 2)

$t_{d(on)}$	Turn-On Delay Time			10	19	ns
$t_r$	Turn-On Rise Time	$V_{DD} = 15\text{ V}$ , $I_D = 1\text{ A}$ ,		7	13	ns
$t_{d(off)}$	Turn-Off Delay Time	$V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\ \Omega$		29	46	ns
$t_f$	Turn-Off Fall Time			12	21	ns
$Q_g$	Total Gate Charge			13	18	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS} = 15\text{ V}$ , $I_D = 12\text{ A}$ , $V_{GS} = 5\text{ V}$		3.5		nC
$Q_{gd}$	Gate-Drain Charge			5.1		nC

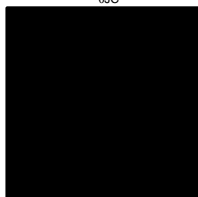
## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Drain–Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain–Source Diode Forward Current				2.3	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.3\text{ A}$ (Note 2)		0.76	1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 12\text{ A}, d_I/d_t = 100\text{ A}/\mu\text{s}$		24		nS
$Q_{rr}$	Diode Reverse Recovery Charge			13		nC

**Notes:**

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $R_{\theta JA} = 45^\circ\text{C}/\text{W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $R_{\theta JA} = 96^\circ\text{C}/\text{W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%

3. Maximum current is calculated as: 
$$\sqrt{\frac{P_D}{R_{DS(ON)}}}$$

where  $P_D$  is maximum power dissipation at  $T_C = 25^\circ\text{C}$  and  $R_{DS(on)}$  is at  $T_{J(max)}$  and  $V_{GS} = 10\text{V}$ . Package current limitation is 21A

DISCONTINUED

THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN

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## Typical Characteristics

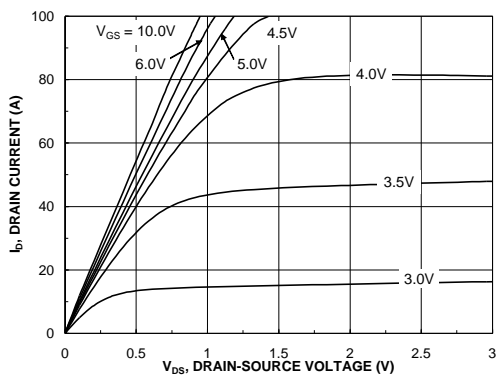


Figure 1. On-Region Characteristics

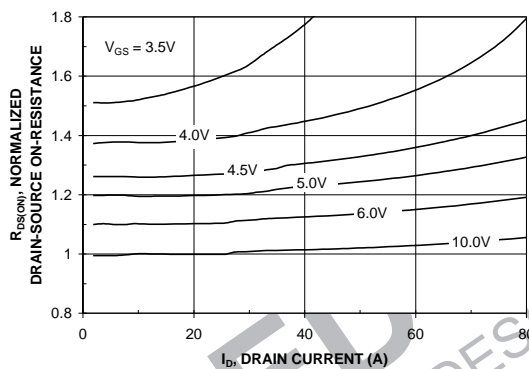


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

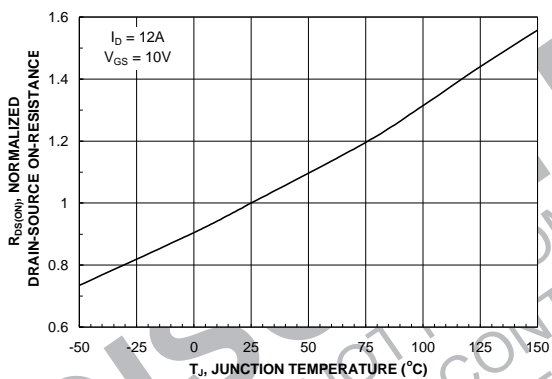


Figure 3. On-Resistance Variation with Temperature

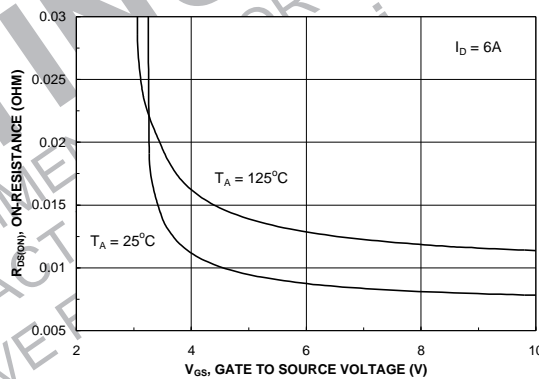


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

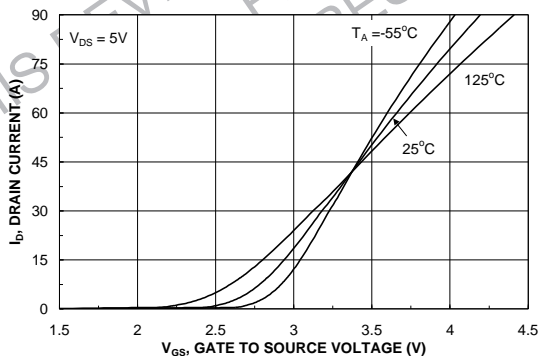


Figure 5. Transfer Characteristics

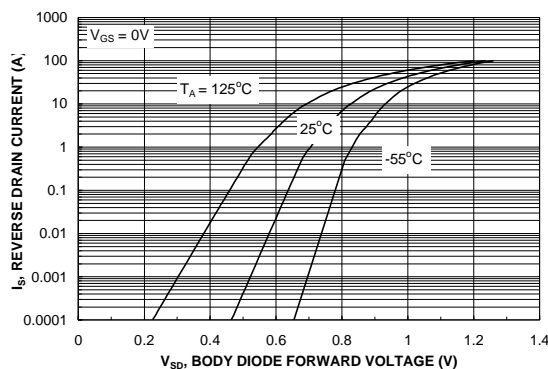


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

### Typical Characteristics

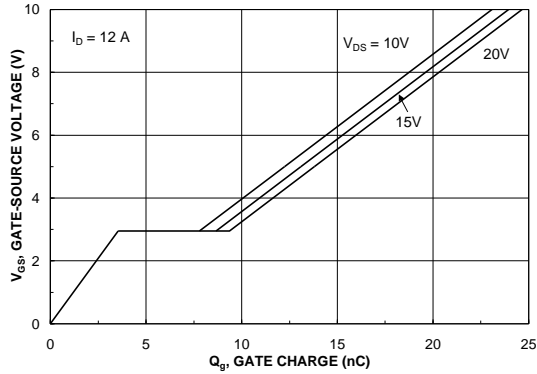


Figure 7. Gate Charge Characteristics

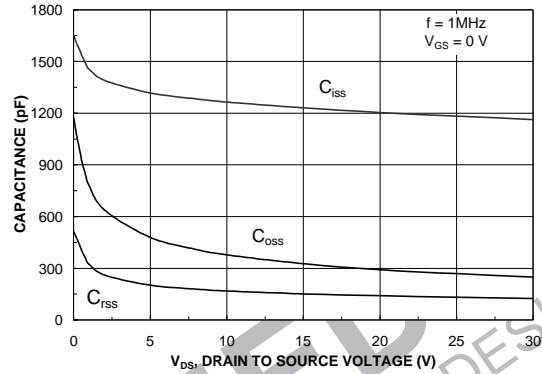


Figure 8. Capacitance Characteristics

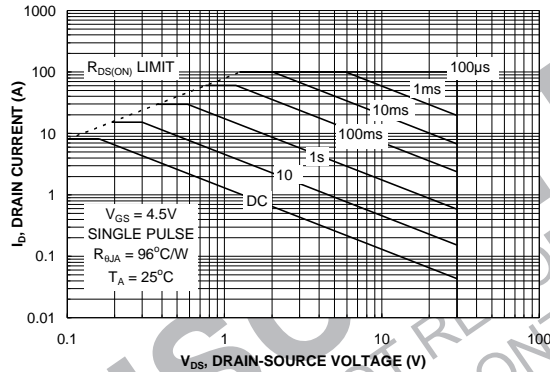


Figure 9. Maximum Safe Operating Area

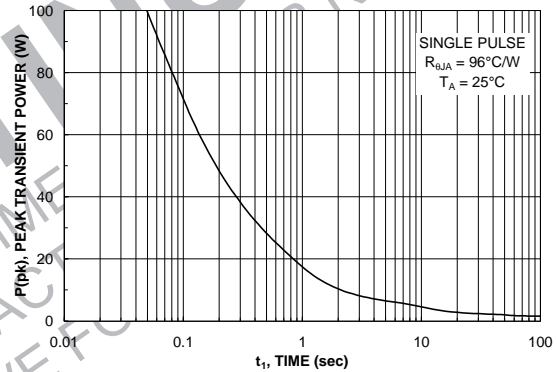


Figure 10. Single Pulse Maximum Power Dissipation

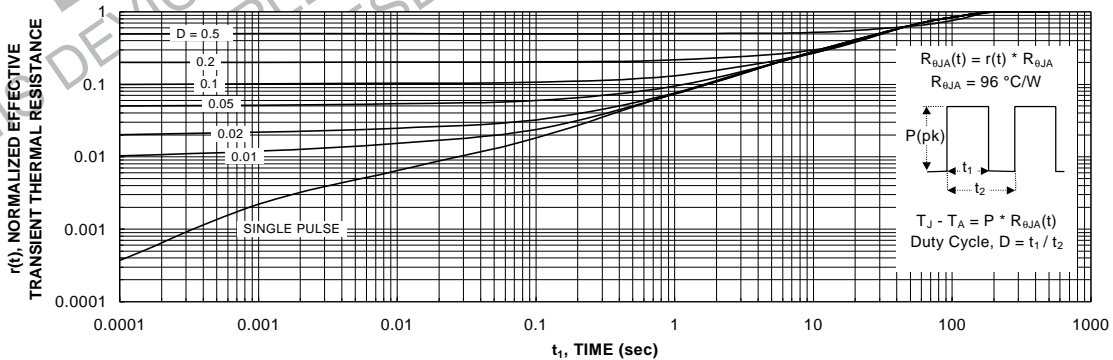


Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b.  
Transient thermal response will change depending on the circuit board design.

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